

Aqueous Alkaline Cleaning Compositions and Methods of Their Use

Field of the Invention

5 The present invention relates to new aqueous alkaline cleaning compositions for processing substrates useful for fabricating electrical and optical devices, in particular electrical devices, including compositions useful for surface preparation, pre-plating cleaning, post-etch cleaning and post-chemical mechanical polishing cleaning.

10 Moreover, the present invention relates to new methods for processing substrates useful for fabricating electrical and optical devices, in particular electrical devices, including new methods for surface preparation, pre-plating cleaning, post-etch cleaning and post-chemical polishing cleaning, which new methods make use of the new aqueous alkaline cleaning compositions.

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Cited Documents

The documents cited in the present application are incorporated by reference in their entirety.

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Description of the Prior Art

The fabrication of electrical devices, in particular, semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; preferably ICs with LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin oxide (ITO); optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks; requires high precision methods which involve inter alia surface preparation, pre-plating cleaning, post-etch cleaning and/or post-chemical polishing cleaning steps using high-purity cleaning compositions.

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Particular care has to be taken in the fabrication of ICs with LSI or VLSI. The semiconductor wafers used for this purpose include a semiconductor substrate such as silicon, into which regions are patterned for the deposition of different materials having electrically insulative, conductive or semiconductive properties.

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In order to obtain the correct patterning, excess material used in forming the various layers on the substrates must be removed. Further, to fabricate functional and reliable ICs, it is important to have flat or planar semiconductor wafer surfaces. Thus, it is necessary to remove and/or polish certain surfaces of a semiconductor wafers during the
10 fabrication of the ICs before carrying out the next process steps.

Chemical Mechanical Polishing or Planarization (CMP) is a process in which material is removed from a substrate surface, as for example, the surface of a semiconductor wafer, and the surface is polished (planarized) by coupling a physical process such as abrasion
15 with a chemical process such as oxidation or chelation. In its most rudimentary form, CMP involves applying a slurry, i.e. a suspension of an abrasive and an active chemistry, to a polishing pad that buffs the surface of a semiconductor wafer to achieve the removal, planarization and polishing. It is not desirable for the removal or polishing to be comprised of purely physical or purely chemical action, but rather the synergistic combination of both
20 in order to achieve a fast uniform removal. In the fabrication of ICs, the CMP slurry should also be able to preferentially remove films that comprise complex layers of metals and other materials so that highly planar surfaces can be produced for subsequent photolithography, patterning, etching and thin-film processing.

25 Nowadays, copper is increasingly used for metal interconnects in ICs. In the copper damascene or dual damascene process commonly used for the metallization of circuitry in the semiconductor fabrication, the layers that must be removed and planarized include copper layers having a thickness of about 1-1.5 μm and copper seed layers having a thickness of about 0.05-0.15 μm . These copper layers are separated from the low-k and
30 ultra low-k dielectric material by a layer of barrier material, typically about 5 to 30 nm thick, which prevents diffusion of copper into the low-k or ultra low-k dielectric material. The key to obtaining good uniformity across the wafer surface after polishing is to use a CMP slurry that has the correct removal selectivities for each material.

35 The foregoing processing operations involving wafer substrate surface preparation, deposition, plating, etching and chemical mechanical polishing variously require cleaning

operations to ensure that the ICs are free from contaminants that would otherwise deleteriously affect the function of the ICs, or even render them useless for their intended functions.

- 5 One particularly grave issue are the residues that are left on the substrates following CMP processing. Such residues include CMP material and corrosion inhibitor compounds such as benzotriazole (BTA). Thus, the copper ion concentration can exceed the maximum solubility of the copper-inhibitor complexes during CMP. Therefore, the copper-inhibitor complexes can precipitate from solution and can coagulate into a surface residue.
- 10 Moreover, these residues can stick to the surface of the polishing pad and accumulate to eventually filling the grooves in the polishing pad. Additionally, abrasive particles and chemicals contained in the CMP slurries as well as reaction by-products can be left behind on the wafer surface. Furthermore, the polishing of copper damascene structures containing ultra low-k dielectric materials such as carbon-doped oxides or organic films
- 15 can generate carbon-rich particles that settle on to the wafer surface. Of course, all these residues can also contaminate the processing tools employed in the process which come into contact with the CMP slurries. To make matters worse these ultra low-k dielectric materials as well as silicon carbide, silicon nitride or silicon oxynitride CMP stop layers are very hydrophobic and hence are difficult to clean with water-based cleaning solutions.

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All these residues can cause a severe roughening of the copper metallization, which has to be avoided since this causes a poor electrical performance.

- Another residue-producing process common to IC manufacturing involves gasphase
- 25 plasma etching to transfer the patterns of developed photoresist coatings to the underlying layers, which may consist of hardmask, interlevel dielectric and etch-stop layers. Post gasphase plasma etch residues, which may include chemical elements present on and in the substrate and in the plasma gases, are typically deposited on the back end of the line (BEOL) structures and, if not removed, may interfere with the subsequent silicidation and
- 30 contact formation.

In order to ameliorate these problems at least to a certain extent, aqueous alkaline cleaning and stripping compositions containing quaternary ammonium hydroxides had been developed and were disclosed in the prior art.

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Thus, the American patent US 6,465,403 B1 discloses aqueous alkaline compositions for stripping or cleaning semiconductor wafer substrates which contain

- bases such as quaternary ammonium hydroxides,
- 5 - metal ion-free silicates such as quaternary ammonium silicates, and
- metal chelating agents

as the obligatory ingredients. The compositions may furthermore contain

- 10 - organic solvents, and
- non-ionic, anionic, cationic and amphoteric surfactants.

The non-ionic surfactants can be selected from the group consisting of acetylenic alcohols, ethoxylated acetylenic alcohols, fluorinated alkyl esters, fluorinated
15 polyoxyethylene alkanols, aliphatic acid esters of polyhydric alcohols, polyoxyethylene monoalkyl ethers, polyoxyethylene diols, polyoxyethylene esters, siloxane type surfactants and alkylene glycol monoalkyl ethers.

In particular, Example 29, column 47, line 10 to column 49, line 8 in conjunction with the
20 Table 28 discloses the solution S8 which consists of

- de-ionized water,
- tetramethylammonium silicate,
- tetramethylammonium hydroxide,
- 25 - trans-(1,2-cyclohexylenenitrilo)-tetraacetic acid, and
- cysteine as a potential titanium residue removal enhancer.

However, the test results presented in the Table 28 show that cysteine has no beneficial effect.

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The American patent application US 2005/0181961 A1 and the American patent US 7,435,712 B2 disclose aqueous alkaline CMP cleaning compositions containing

- cleaning agents such as tetraalkylammonium hydroxide,
- 35 - complexing agents such as cysteine or ethylenediamine and
- corrosion-inhibiting compounds such as cysteine

as the obligatory ingredients. The compositions may furthermore contain non-ionic, anionic, cationic or amphoteric surfactants or mixtures thereof. However, the surfactants are not specified nearer.

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The American patent application US 2006/0166847 A1, page 5, paragraphs [0082] and [0083] discloses the aqueous alkaline cleaning composition K containing inter alia

- ethanolamine,
- 10 - tetramethylammonium hydroxide and
- cysteine;

and the aqueous cleaning composition M containing inter alia

- 15 - ethanolamine,
- tetramethylammonium hydroxide and
- ethylenediamine.

However, as can be taken from page 8, Table 1 in conjunction with paragraph [0161], both
20 compositions exhibit only a poor cleaning efficiency. Moreover, according to page 12, Example 13, paragraph [0198] in conjunction with the Figure 9, the said aqueous alkaline cleaning compositions also cause a high roughness of the treated copper surfaces.

The prior art aqueous alkaline cleaning or stripping compositions are susceptible to
25 degradation when exposed to oxygen, which in turn results in darkening of the color of the compositions, with the result that sensors associated with the fabrication process tools yield erroneous outputs that can compromise the function and reliability of the tool. Additionally, such degradation involves the loss of cleaning and/or stripping power. This can become so extensive in the case of prolonged oxygen exposure that the cleaning or
30 stripping composition has no longer a significant efficacy.

The prior art discussed above does not offer any hints as to how these problems may be resolved. In particular, it appears that ingredients such as cysteine or ethylenediamine at best offer no advantages if they are not altogether disadvantageous as demonstrated by
35 the international patent application WO 2006/081406 A1 or the American patent application US 2006/0166847 A1 discussed above.

As regards cysteine, it is well known in the art that this compound is easily oxidized (cf., for example, Shayne C. Gad, Handbook of Pharmaceutical Biotechnology, John Wiley and Sons, 2007, page 328). Moreover, traces of heavy metals in particular iron and copper can decompose cysteine (cf. Römpp Online 2009, "L-cysteine"). Consequently,
5 one would even less so expect that aqueous alkaline cleaning compositions could ameliorate the problems described above.

The international patent application WO 2005/093031 A1 discloses an improved acidic
10 chemistry for post-CMP cleaning. The acidic cleaning solution is in the neutral to low pH range and comprises a cleaning agent such as cysteine or salicylic acid and a corrosion-inhibiting compound such as as cysteine. However, such acidic chemistry tends to attack metallic surfaces to a much greater extent, in particular in the presence of complexing agents and oxygen. Therefore, the skilled artisan can derive nothing from the international
15 patent application as to how he could increase the undesirably low stability of the alkaline cleaning compositions containing cysteine.

The prior international patent application PCT/EP2010/058422 filed on June 16, 2010 and claiming the priority of the US provisional patent application Serial No. 61/221,807 filed on
20 June 30, 2009 describes aqueous alkaline cleaning compositions containing

- (A) at least one thioamino acid having at least one primary amino group and at least one mercapto group,
- 25 (B) at least one quaternary ammonium hydroxide,
- (C) at least one chelating and/or corrosion inhibiting agent selected from the group consisting of aliphatic and cycloaliphatic amines having at least two primary amino groups, aliphatic and cycloaliphatic amines having at least one hydroxy group, and
30 aromatic compounds having at least one acid group and at least one hydroxy group, and
- (D) at least one organic solvent having wetting properties and a melting point below 0°C

as the obligatory ingredients. The compositions may furthermore contain functional additives (E) which are different from the essential components (A), (B), (C) and (D) and which can be selected from the group consisting of corrosion inhibitors, bases, titanium residue removal enhancers, organic solvents, alcohols having at least one mercapto
5 group, complexing or chelating agents, surfactants and metal free silicates as described in the American patents US 6,465,403 B1, column 7, line 1 to column 8, line 65; US 6,200,947 B1, column 2, lines 29 to 40, US 6,194,366 B1, column 3, lines 55 to 60, and US 6,492,308 B1, column 3, lines 1 to 9, and the American patent application US 2005/0181961 A1, page 2, paragraph [0019].

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Objects of the Invention

It was an object of the present invention to provide novel aqueous alkaline cleaning compositions for processing substrates useful for fabricating electrical devices, in
15 particular, semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips, micro plants and magnetic heads; more preferably ICs with LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin
20 oxide (ITO); optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks, which fabrication requires high precision methods involving inter alia surface preparation, pre-plating cleaning, post-etch cleaning and/or
25 post-CMP cleaning steps using high-purity cleaning compositions.

In particular, the novel aqueous alkaline cleaning compositions should no longer exhibit the disadvantages of the prior art compositions such as too fast a discoloration, darkening and decomposition upon exposure to oxygen so that they can be easily prepared, stored,
30 transported, handled and used even after a comparatively long storage without loss of cleaning and/or stripping power and without causing erroneous outputs of the sensors associated with the fabrication process tools, which outputs can compromise the function and reliability of the tools.

35 The novel aqueous alkaline cleaning compositions ought to be particularly well-suited for carrying out the above-mentioned cleaning steps, in particular, the post-CMP cleaning of

semiconductor wafers during the fabrication of ICs with LSI or VLSI, in particular via the copper damascene or dual damascene process.

The novel aqueous alkaline cleaning compositions ought to remove most efficiently all
5 kinds of residues and contaminants generated during the substrate surface preparation, deposition, plating, etching and CMP to ensure that the substrates, in particular the ICs, are free from residues and contaminants that would otherwise deleteriously affect the functions of the electrical and optical devices, in particular the ICs, or render them even
10 useless for their intended functions. In particular, they should prevent the roughening of the copper metallization in damascene structures.

Moreover, the novel aqueous alkaline cleaning compositions ought to remove most efficiently such residues and and contaminants not only from the substrates but also from the fabrication tools which are used in the various processes.

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It was another object of the invention to provide novel methods for processing substrates useful for fabricating electrical devices, in particular, semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; more preferably ICs with
20 LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin oxide (ITO); optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser
25 LEDs; semiconductor monocrystals; and glass substrates for magnetic disks, which novel methods make use of the novel aqueous alkaline cleaning compositions.

In particular, the novel methods for fabricating electrical and optical devices, in particular electrical devices, ought to involve surface preparation, pre-plating cleaning, post-etch
30 cleaning and/or post-CMP cleaning steps, more particularly post-etch and/or post-CMP cleaning steps, and, most particularly, post-CMP cleaning steps using the novel aqueous alkaline cleaning compositions.

The novel methods for fabricating electrical devices ought to be particularly well-suited for
35 the fabrication of ICs with LSI or VLSI, especially with the help of the copper damascene and dual damascene process. Regarding the copper damascene and dual damascene

process, the novel methods ought to remove contaminants and residues such as particles consisting of or containing copper, copper oxide, copper-inhibitor complexes, abrasives and carbon after the CMP step from the substrate surfaces, the polishing pads and other processing tools most efficiently without scratching, etching and roughening the copper surfaces.

Summary of the Invention

Accordingly, the novel aqueous alkaline cleaning compositions free from organic solvents and metal ion-free silicates were found, the said compositions comprising

- (A) at least one thioamino acid having at least one primary amino group and at least one mercapto group,
- (B) at least one quaternary ammonium hydroxide,
- (C) at least one chelating and/or corrosion inhibiting agent selected from the group consisting of aliphatic and cycloaliphatic amines having at least two primary amino groups, and aliphatic and cycloaliphatic amines having at least one hydroxy group,
- (D) at least one nonionic surfactant selected from the group of acetylenic alcohols, alkyloxylated acetylenic alcohols and alkyloxylated sorbitan monocarboxylic acid mono esters.

Hereinafter the novel aqueous alkaline cleaning compositions are referred to as the "compositions of the invention".

Moreover, the novel methods for processing substrates useful for fabricating electrical and optical devices were found, the said methods making use of at least one composition of the invention in at least one process step.

Hereinafter the novel methods for processing substrates useful for fabricating electrical and optical devices are referred to as the "methods of the invention".

Last but not least, the novel use of the composition of the invention for the processing of substrates useful for fabricating electrical and optical devices has been found.

Advantages of the Invention

In view of the prior art discussed above, it was surprising and could not be expected by
5 the skilled artisan that the objects underlying the present invention could be solved by the compositions and the methods of the invention.

It was particularly surprising that the compositions of the invention were excellently suited for processing substrates useful for fabricating electrical devices, in particular,
10 semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; more preferably ICs with LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin oxide (ITO);
15 optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks.

20 It was even more surprising that the compositions of the invention were most excellently suited for high precision fabrication methods involving inter alia surface preparation, pre-plaiting cleaning, post-etch cleaning and/or post-CMP cleaning steps.

The compositions of the invention themselves no longer exhibited the disadvantages of
25 the prior art compositions such as too fast a discoloration, darkening and decomposition upon exposure to oxygen so that they could be easily prepared, stored, transported, handled and used even after a comparatively long storage without loss of cleaning and/or stripping power and without causing erroneous outputs of the sensors associated with the fabrication processing tools, which outputs compromised the function and reliability of the
30 processing tools.

The compositions of the invention were most particularly well-suited for carrying out the above-mentioned cleaning steps, in particular, the post-CMP cleaning of semiconductor wafers and the fabrication of ICs with LSI or VLSI, in particular by the copper damascene
35 or dual damascene process.

The compositions of the invention removed most efficiently all kinds of residues and contaminants generated during the substrate surface preparation, deposition, plating, etching and CMP and ensured that the substrates, in particular the ICs, were free from residues and contaminants that would have otherwise deleteriously affected the functions of the electrical and optical devices, in particular the ICs, or would have rendered them even useless for their intended functions. In particular, they prevented the scratching, etching and roughening of the copper metallization in damascene structures.

Moreover, the compositions of the invention removed such residues and contaminants most efficiently not only from the substrates but also from processing tools used in the various fabrication processes.

It was most particularly surprising that the methods of the invention were most excellently suited for fabricating electrical devices, in particular, semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; more preferably ICs with LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin oxide (ITO); optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks.

In particular, the methods of the invention were most excellently suited for the fabrication of electrical and optical devices, in particular electrical devices, which fabrication involved surface preparation, pre-plating cleaning, post-etch cleaning and/or post-CMP cleaning steps, more particularly post-etch and/or post-CMP cleaning steps, and, most particularly, post-CMP cleaning steps.

The methods of the invention were most particularly well-suited for the fabrication of ICs with LSI or VLSI, especially with the help of the copper damascene and dual damascene process. Regarding the copper damascene and dual damascene process, the methods of the invention removed contaminants and residues such as particles containing or consisting of copper, copper oxide, copper-inhibitor complexes, abrasives and carbon after the CMP steps from the substrate surfaces, the polishing pads and other processing tools most efficiently without scratching, etching and roughening the copper surfaces.

Detailed Description of the Invention

In its broadest aspect the present invention relates to the compositions of the invention.

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The compositions of the invention are aqueous alkaline cleaning compositions for processing substrates useful for fabricating electrical and optical devices.

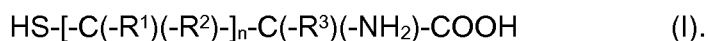
"Aqueous" means that the compositions of the invention contain water. The water content
10 can vary broadly from composition to composition.

"Alkaline" means that the compositions of the invention have a pH in the range of from 8 to 14, preferably 9 to 13 and, most preferably, 8.5 to 12.5.

15 The compositions of the invention comprise as the first essential component at least one, preferably one thioamino acid (A) having at least one, preferably one primary amino group and at least one, preferably one mercapto group. The thioamino acid (A) may be an synthetic or naturally occurring, preferably a naturally occurring amino acid. More preferably, the thioamino acid (A) is an alpha-amino acid. Even more preferably, the
20 mercapto group of the thioamino acid (A) is in the gamma-position. Most preferably, the thioamino acid (A) is an alpha-amino acid having the mercapto group in the gamma-position.

Most particularly preferably, the thioamino acid (A) has the general formula I:

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In the general formula I the index n is an integer of 1 to 3, preferably 1 or 2. Most preferably, n equals 1.

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The residues R^1 and R^2 of the general formula I are selected independently from each other from the group consisting of

- hydrogen atoms;

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- straight and branched, saturated and unsaturated, preferably saturated, substituted and unsubstituted, preferably unsubstituted aliphatic residues having 1 to 10 carbon atoms, preferably alkyl residues, in particular methyl, ethyl, propyl, isopropyl, n-butyl, isobutyl, sec-butyl, tert-butyl, pentyl, 1-methyl butyl, 2-methyl butyl, 3-methyl butyl, 1-ethyl propyl, 1,2-dimethyl propyl, 2,2-dimethyl propyl, hexyl, heptyl, octyl, iso-octyl, nonyl or decyl;
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- substituted and unsubstituted, preferably unsubstituted, saturated and unsaturated, preferably saturated cycloalkyl residues having 3 to 8 carbon atoms, in particular cyclopropyl, cyclobutyl, cyclopentyl, cyclohexyl, cycloheptyl, cyclooctyl and residues derived from bicyclo[2.2.1]cycloheptane or norcarane;
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- substituted and unsubstituted, preferably unsubstituted, saturated and unsaturated, preferably saturated alkylcycloalkyl residues wherein the alkyl group is having from 1 to 4 carbon atoms and the cycloalkyl group is having from 3 to 8 carbon atoms, in particular residues derived from methyl-, ethyl-, propyl-, isopropyl- or butyl-substituted cyclopropane, cyclobutane or cyclohexane, pinane or bornane, which alkylcycloalkyl residues may be linked to the basic structure of the thioamino acid (A) of the general formula I via a carbon atom of the alkyl group or via a carbon atom of the cycloalkyl group;
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20
- substituted and unsubstituted, preferably unsubstituted aryl residues having from 6 to 16 carbon atoms, in particular phenyl or naphthyl or residues derived from anthracene or phenanthrene;
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- substituted and unsubstituted, preferably unsubstituted alkylaryl residues wherein the alkyl group is having from 1 to 4 carbon atoms and the aryl group is having from 6 to 16 carbon atoms, in particular methyl-, ethyl-, propyl-, isopropyl- or butyl-substituted phenyl or naphthyl or residues derived from methyl-, ethyl-, propyl-, isopropyl- or butyl-substituted anthracene or phenanthrene which alkylaryl residues may be linked to the basic structure of the thioamino acid (A) of the general formula I via a carbon atom of the alkyl group or via a carbon atom of the aryl group;
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- substituted and unsubstituted, preferably unsubstituted cycloalkylaryl residues wherein the cycloalkyl group is having from 3 to 8 carbon atoms and the aryl group
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is having from 6 to 16 carbon atoms, in particular cyclopropyl-, cyclobutyl-, cyclopentyl-, cyclohexyl-substituted phenyl, which cycloalkylaryl residues may be linked to the basic structure of the thioamino acid (A) of the general formula I via a carbon atom of the cycloalkyl group or via a carbon atom of the aryl group;

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- substituted and unsubstituted, preferably unsubstituted heteroaryl residues having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms, in particular residues derived from furane, xanthene, thiophene, pyrrole, imidazole, triazoles, tetrazole, pyridine, pyridazine, pyrimidine, pyrazene, triazines, tetrazines, indole, quinoline, isoquinoline, purine or phosphinine;

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- substituted and unsubstituted, preferably unsubstituted alkylheteroaryl residues wherein the alkyl group is having from 1 to 4 carbon atoms, in particular the alkyl groups described hereinbefore, and the heteroaryl group is having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms, in particular the heteroaryl groups as described hereinbefore, which alkylheteroaryl residues may be linked to the basic structure of the thioamino acid (A) via a carbon atom of the alkyl group or via a carbon atom of the heteroaryl group;

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- substituted and unsubstituted, preferably unsubstituted cycloalkylheteroaryl residues wherein the cycloalkyl group is having from 3 to 8 carbon atoms, in particular the cycloalkyl groups as described hereinbefore, and the heteroaryl group is having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms, in particular the heteroaryl groups as described herein before; and

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- substituted and unsubstituted, preferably unsubstituted arylheteroaryl residues wherein the aryl group is having from 6 to 16 carbon atoms, in particular the aryl groups as described hereinbefore, and the heteroaryl group is having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms, in particular the heteroaryl groups as described herein before.

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- 35 Alternatively, the residues R¹ and R² together form a saturated or unsaturated, preferably saturated, substituted or unsubstituted, preferably unsubstituted ring having 3 to 6 carbon

atoms, wherein no carbon atom or 1 or 2 carbon atoms is or are replaced by one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms.

- 5 The residue R^3 of the general formula I is a single residue R^1 or R^2 or a covalent bond or bivalent group linking the carbon atom carrying the amino group and the carboxyl group to one of the residues R^1 or R^2 or to the ring formed by the residues R^1 and R^2 . The bivalent linking group is stable in the presence of the quaternary ammonium salt (B), which means that it does not hydrolyze or hydrolyzes only very slowly to a very small extent so that the
- 10 concentration of the hydrolyzation products is so low that they do not interfere with the function of the compositions of the invention.

Preferably, the bivalent linking group is selected from the group consisting of:

- 15 -O-, -C(O)-, -C(S)-, -C(O)-O-, -O-C(O)-O-, -O-C(S)-O-;
 -NR¹-, =N-, -N=N-, -NR¹-C(O)-, -NR¹-NR¹-C(O)-, -NR¹-NR¹-C(S)-, -O-C(O)-NR¹-,
 -O-C(S)-NR¹-, -NR¹-C(O)-NR¹-, -NR¹-C(S)-NR¹-;
 -S-, -S(O)-, -S(O)₂-, -O-S(O)₂-, and -NR¹-S(O)₂-;

- 20 wherein the residue R^1 is having the above-described meaning.

- Generally, the substituted residues R^1 , R^2 and R^3 described above can contain any substituents as long as the substituents are stable in the presence of the quaternary ammonium hydroxide (B), which means that they do not hydrolyze or hydrolyze only very
- 25 slowly to a very small extent and do not cause any undesired reactions which could lead to the decomposition and/or the agglomeration and/or the formation of precipitates in or of the compositions of the invention. Preferably, the substituents are selected from the group consisting of:

- 30 -OR¹, -C(O)-R¹, -COOR¹, -SO₃R¹, -P(O)₂R¹, -N(-R¹)₂,
 -NR¹-C(O)(-R¹)₂;
 -F, -Cl, -CN and -NO₂;

wherein the residue R^1 is having the above-described meaning.

Additional examples for thioamino acids (A) of the general formula I are known from the international patent application WO 02/22568, page 13, line 9, to page 16, line 12.

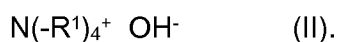
The thioamino acids (A) of the general formula I can be racemic or enantiomeric mixtures
5 which may be equimolar or non-equimolar, or one of the respective enantiomers or diastereomers.

More preferably, at least one of the residues R^1 , R^2 and R^3 described above is a hydrogen atom. Even more preferably, all of the residues R^1 , R^2 and R^3 are hydrogen atoms.

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Therefore, most preferably, the thioamino acid (A) is selected from cysteine and homocysteine, in particular, cysteine, especially L-cysteine.

The compositions of the invention comprise as the second essential component at least
15 one, preferably one quaternary ammonium hydroxide (B). More preferably, the quaternary ammonium hydroxide (B) has the general formula II:



20 In the general formula II, the residue R^1 is having the above defined meaning except hydrogen atom, whilst all the residues R^1 are the same or at least two residues R^1 are different from each other and all the residues R^1 are single residues or at least two residues R^1 form a saturated or unsaturated, substituted or unsubstituted ring having 3 to 6 carbon atoms, wherein no carbon atom or 1 or 2 carbon atoms are replaced by one
25 hetero atom selected from the group of oxygen, sulfur, nitrogen and phosphorus atoms.

More preferably, the residue R^1 of the general formula II is selected from the group consisting of straight and branched, substituted and unsubstituted, saturated aliphatic residues having 1 to 10, in particular, 1 to 4 carbon atoms.

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In the case that the quaternary ammonium hydroxide (B) of the general formula II only contains residues R^1 which are unsubstituted and saturated, all residues R^1 are preferably the same.

In the case that the quaternary ammonium hydroxide (B) of the general formula II contains residues R^1 which are a substituted and saturated, it is preferred that only one of the residues R^1 is substituted.

- 5 Particularly preferably, the quaternary ammonium hydroxide (B) of the general formula II contains methyl, ethyl, propyl, isopropyl, n-butyl, sec-butyl, iso-butyl, tert-butyl, n-pentyl, 2-hydroxyethyl, 2- and 3-hydroxypropyl and/or 4-hydroxy-n-butyl groups, in particular, methyl and/or 2-hydroxyethyl groups.
- 10 Most particularly preferably, tetramethylammonium hydroxide (TMAH) and/or choline, especially TMAH, is or are used.

- The compositions of the invention contain as the third essential component at least one chelating and/or corrosion inhibiting agent (C) selected from the group consisting of
- 15 aliphatic and cycloaliphatic amines having at least two, preferably two primary amino groups, and aliphatic and cycloaliphatic amines having at least one, preferably one hydroxy group.

- Preferably, the aliphatic amine (C) having at least two primary amino groups is selected
- 20 from the group consisting ethylenediamine, propylenediamine, n-butylenediamine, diethylenetriamine, dipropylenetriamine, di-n-butylenetriamine, triethylenetetraamine, tripropylenetetraamine, and tri-n-butylenetetraamine, more preferably ethylenediamine and diethylenetriamine, most preferably ethylenediamine or diethylenetriamine.

- 25 Preferably, the cycloaliphatic amine (C) is selected from the group consisting of 1,2-, 1,3- and 1,4-diamino cyclohexane;

- Preferably, the aliphatic amine (C) having at least one hydroxy group is selected from the group consisting of ethanolamine, diethanolamine and triethanolamine, most preferably
- 30 ethanolamine.

Preferably, the cycloaliphatic amine (C) having at least one hydroxy group is selected from the group consisting of 2-, 3- and 4-hydroxy cyclohexylamine.

- 35 Particularly preferably, the chelating and/or corrosion inhibiting agent (C) is selected from the group consisting of ethylenediamine and diethylenetriamine.

The compositions of the invention comprise as the fourth essential component at least one, preferably one nonionic surfactant (D) selected from the group of

- 5 - acetylenic alcohols, preferably acetylenic monoalcohols and diols;
- alkyloxyated, preferably ethoxylated, acetylenic alcohols, preferably acetylenic monoalcohols and diols; and
- alkyloxyated, preferably ethoxylated, sorbitan monocarboxylic acid mono esters, preferably fatty acid mono esters.

10

Most preferably, the acetylenic monoalcohols and diols (D) and their ethoxylated derivatives (D) are selected from the group consisting of 3,5-dimethyl-1-hexyne-3-ol, 2,4,7,9-tetramethyl-5-decyne-4,7-diol and 2,5,8,11-tetramethyl-6-dodecyne-5,8-diol, and their ethoxylated derivatives.

15

More preferably, the ethoxylated sorbitan fatty acid mono esters (D) are selected from the group consisting of ethoxylated sorbitan fatty acid mono esters having 20 to 100, most preferably 20 to 80 ethoxy groups to the molecule. More preferably, the fatty acid residues are selected from the group consisting of fatty acid residues having 10 to 20 carbon
20 atoms. Most preferably, the fatty acid residues are selected from the group consisting of laurate, palmitate, stearate and oleate.

Optionally, the compositions of the invention can contain at least one functional additive (E) which is different from the essential components (A), (B), (C) and (D). Preferably, the
25 functional additive (E) is selected from the group consisting of corrosion inhibitors, bases, complexing or chelating agents, film forming agents, surfactants and pH-adjusting agents.

Preferably, the complexing or chelating, film-forming and/or corrosion inhibiting agent (E) is selected from the group consisting of aromatic compounds having at least one, preferably one acid group, in particular at least one, preferably one carboxylic acid group, and at least one, preferably one hydroxy group, and nitrogen containing cyclic
30 compounds.

More preferably, the aromatic compound (C) having at least one, preferably one
35 carboxylic acid group and at least one, preferably one hydroxy group is selected from the

group consisting of salicylic acid, 3- and 4-hydroxy phthalic acid, 2-hydroxy terephthalic acid, and 3-, 4-, 5- and 6-hydroxysalicylic acid, most preferably salicylic acid.

More preferably, the nitrogen containing cyclic compound (E) is selected from the group consisting of imidazole, triazole, benzotriazole, benzimidazole and benzothiadiazole and their derivatives with hydroxy, amino, imino, carboxy, mercapto, nitro and alkyl substituents, in particular 1,2,4-triazole.

More preferably, the surfactants (E) are selected from the group consisting of customary and known nonionic, and ionic, cationic and amphoteric surfactants as described, for example, in the American patents US 6,465,403 B1, column 8, lines 17 to 65.

More preferably, the base (E) is ammonia.

More preferably, the pH-adjusting agent (E) is selected from the group of aliphatic carboxylic acids, preferably formic acid, acetic acid, propionic acid, lactic acid, tartaric acid and citric acid.

The compositions of the invention can contain the essential components (A), (B), (C) and (D) and optionally (E) in broadly varying amounts. Thus, the compositions of the invention can be highly concentrated solutions which contain only small amounts of water.

Preferably, the compositions of the invention are diluted or highly diluted aqueous compositions, i.e., they contain more than 50% by weight, more preferably more than 75% by weight and, most preferably, more than 90% by weight of water, each weight percentage being based on a complete weight of a composition of the invention.

The concentration of the thioamino acid (A) in the composition of the invention can vary broadly and, therefore, can be adjusted most advantageously to the requirements of the particular composition of the invention and method of the invention. Preferably, the composition of the invention contains, based on the complete weight of the composition, 0.1 to 20% by weight, more preferably 0.1 to 15% by weight and, most preferably, 0.1 to 10% by weight of the thioamino acid (A).

Likewise, the concentration of the quaternary ammonium hydroxide (B) in the composition of the invention can vary broadly and, therefore, can be adjusted most advantageously to

the requirements of a particular composition of the invention and method of the invention. Preferably, the composition of the invention contains, based on the complete weight of the composition, 0.1 to 20% by weight, more preferably 0.1 to 15% by weight and, most preferably, 0.1 to 10% by weight of the quaternary ammonium hydroxide (B).

5

Moreover, the concentration of the chelating and/or corrosion inhibiting agent (C) in the composition of the invention can vary broadly and, therefore, can be adjusted most advantageously to the requirements of a particular composition of the invention and method of the invention. Preferably, the composition of the invention contains, based on
10 the complete weight of the composition, 0.05 to 15 % by weight, more preferably 0.1 to 12.5% by weight and, most preferably, 0.1 to 10% by weight of the chelating and/or corrosion inhibiting agent (C).

Also the concentration of the nonionic surfactant (D) in the composition of the invention
15 can vary broadly and, therefore, can be adjusted most advantageously to the requirements of a particular composition of the invention and method of the invention. Preferably, the composition of the invention contains, based on the complete weight of the composition, 0.001 to 5% by weight, preferably 0.005 to 4% by weight and most preferably as 0.01 to 3% by weight of the nonionic surfactant (D).

20

Also the concentration of the at least one functional additive (E) can vary broadly and, therefore, can be adjusted most advantageously to the requirements of a composition of the invention and method of the invention. Most preferably, the at least one functional additive (E) is used in the effective concentrations customary and known to the skilled
25 artisan.

The compositions of the invention can be prepared by customary and standard mixing processes and mixing apparatuses such as agitated vessels, in-line dissolvers, high shear impellers, ultrasonic mixers, homogenizer nozzles or counterflow mixers, can be used for
30 carrying out the mixing of the components of the compositions in the desired amounts.

The compositions of the invention are excellently suited for the methods of the invention.

Moreover, the compositions of the invention are also excellently suited for cleaning all
35 kinds of processing tools such as polishing pads, sensors, nozzles, pipes and/or structural

features of the equipment used, which tools come into contact with other processing liquids used in fabricating electrical or optical devices.

The main purpose of the methods of the invention however is the processing of substrates useful for fabricating electrical devices, in particular, semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; more preferably ICs with LSI (large-scale integration) or VLSI (very-large-scale integration); as well as optical devices, in particular, optical glasses such as photo-masks, lenses and prisms; inorganic electro-conductive films such as indium tin oxide (ITO); optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals such as the end faces of optical fibers and scintillators; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks.

It is essential that the methods of the invention make use of at least one composition of the invention in at least one process step.

Preferably, the methods of the invention involve surface preparation, pre-plating cleaning, post-etch cleaning and/or post-CMP cleaning steps, in particular post-CMP cleaning steps.

The methods of the invention are particularly well-suited for the processing of substrates useful for fabricating ICs with LSI or VLSI, in particular in the back end of the line processing (BEOL).

The methods of the invention are most particularly well-suited for the post-CMP cleaning of semiconductor wafers in the fabrication of ICs with LSI or VLSI, in particular by the copper damascene or dual damascene process.

As is known in the art, a typical equipment for the CMP consists of a rotating platen which is covered with a polishing pad. The wafer is mounted on a carrier or chuck with its upper side down facing the polishing pad. The carrier secures the wafer in the horizontal position. This particular arrangement of polishing and holding device is also known as the hard-platen design. The carrier may retain a carrier pad which lies between the retaining surface of the carrier and the surface of the wafer which is not being polished. This pad can operate as a cushion for the wafer.

Below the carrier, the larger diameter platen is also generally horizontally positioned and presents a surface parallel to that of the wafer to be polished. Its polishing pad contacts the wafer surface during the planarization process. During the CMP process of the invention, the CMP agent (A), in particular, the CMP agent of the invention is applied onto the polishing pad as a continuous stream or in dropwise fashion.

Both the carrier and the platen are caused to rotate around their respective shafts extending perpendicular from the carrier and the platen. The rotating carrier shaft may remain fixed in position relative to the rotating platen or may oscillate horizontally relative to the platen. The direction of rotation of the carrier typically, though not necessarily, is the same as that of the platen. The speeds of rotation for the carrier and the platen are generally, though not necessarily, set at different values.

Customarily, the temperature of the platen is set at temperatures between 10 and 70°C.

For further details reference is made to the international patent application WO 2004/063301 A1, in particular page 16, paragraph [0036] to page 18, paragraph [0040] in conjunction with the figure 1.

20

After the CMP step, the surface of the semiconductor wafer is contacted with a composition of the invention for a time and a temperature sufficient to clean the unwanted contaminants and residues from the substrate surface. Optionally, the substrate is rinsed to remove the composition of the invention and the contaminants and residues and dried to remove any excess solvents or rinsing agents.

Preferably, the methods of the invention use a bath or a spray application to expose the substrate to the composition. Bath or spray cleaning times are generally one minute to 30 minutes, preferably 5 minutes to 20 minutes. Bath or spray cleaning temperatures are generally 10°C to 90°C, preferably 20°C to 50°C. However, megasonics and ultrasonic, preferably megasonics cleaning methods can also be applied.

If required, the rinse times are generally 10 seconds to 5 minutes at room temperature, preferably 30 seconds to 2 minutes at room temperature. Preferably, deionized water is used to rinse the substrates.

If required, the drying of the substrates substrates can be accomplished using any combination of air-evaporation, heat, spinning or pressurized gas. The preferred drying technique is spinning under a filtered inert gas flow, such as nitrogen, for a period of time until the substrate is dry.

5

Examples

Examples 1 to 4

10 The Preparation of Aqueous Alkaline Cleaning Compositions Containing L-Cysteine

The aqueous alkaline cleaning compositions of the examples 1 to 4 were prepared by mixing their ingredients and homogenizing the resulting mixtures. The Table 1 summarizes their compositions.

15

Table 1: The Compositions of the Aqueous Alkaline Cleaning Compositions
(Balance: Water)

Example	TMAH ^{a)} / % by weight	DETA ^{b)} / % by weight	Cysteine/ % by weight	Surfactant	Film- forming Agent ^{e)}	pH - adjusting agent ^{f)}
1	10	7	8	0.2 ^{c)}	2	1.5
2	0.5	0.35	0.4	0.01 ^{c)}	0.1	0.07
3	10	7	8	0.2 ^{d)}	2	1.5
4	0.5	0.35	0.4	0.01 ^{d)}	0.1	0.07

- 20 a) tetramethylammonium hydroxide;
 b) diethylenetriamine;
 c) 3, 5-dimethyl-1-hexyn-3-ol;
 d) polyoxyethylene sorbitan laurate;
 e) 1,2,4-triazole;
 25 f) citric acid.

The concentrated compositions of the examples 1 and 3 were stable upon prolonged storage when air was excluded. Therefore, they could be most advantageously manufactured, stored, handled and shipped. Thus, it was possible to deliver the

concentrated compositions most economically to the customer who could easily dilute them before use.

5 The diluted compositions of the examples 2 and 4 were likewise stable even upon comparatively long exposure to oxygen and exhibited a particularly high cleaning efficacy with only a very small change of the surface roughness during the cleaning of copper surfaces.

10 Compositions containing ethylenediamine instead of diethylenetriamine exhibited the same advantageous properties and effects.

Examples 5 to 6

15 The Etching Rates of the Aqueous Alkaline Compositions of the Examples 2 and 4

The composition of the example 2 was used for the example 5 and the composition of the example 4 was used for the example 6.

20 The etching rates were measured by the 4-point probe (Napson) method and confirmed by the atomic force microscopy (AFM).

To this end, pieces of electroless copper deposit (ECD) wafers were immersed in the various aqueous alkaline cleaning compositions at room temperature for 1 hour (4-point probe measurements) or 1 minute (AFM measurements). Thereafter, the ECD wafers
25 were taken from the compositions, rinsed with water and dried in a nitrogen stream at room temperature. The ECD wafers of the examples 5 and 6 were not etched and showed no change in their surface roughness.

30 Compositions containing ethylenediamine instead of diethylenetriamine exhibited the same advantageous properties and effects.

Examples 7 and 8 and Comparative Experiment C1

35 The Cleaning Efficacy of the Aqueous Alkaline Cleaning Compositions of the Examples 2 and 4 (Examples 7 and 8) in Comparison with Deionized Water (Comparative Experiment C1)

The composition of the example 2 was used for the example 7; and the composition of the example 4 was used for the example 8. Deionized water was used for the comparative experiment C1.

5

The cleaning efficacy of the aqueous alkaline cleaning compositions was tested as follows. ECD copper wafer pieces were contaminated with CMP agents containing silica particles having a mean primary particle diameter of 30 nm as measured with the laser light scattering method. Thereafter, the contaminated ECD copper wafer pieces were
10 treated with the compositions of the example 2 or 4 and, for purposes of comparison, with deionized water for one minute each. Thereafter, the surfaces of the treated ECD copper wafer pieces were checked for particle residues by scanning electron microscopy (SEM). Whereas the surfaces of the ECD copper wafer pieces treated with the compositions of the examples 2 and 4 were free from silica particles, the surfaces of the ECD copper
15 wafer pieces treated with deionized water were still covered with considerable amounts of silica particles.

Compositions containing ethylenediamine instead of diethylenetriamine exhibited the same advantageous properties and effects.

Claims

1. Aqueous alkaline cleaning composition free from organic solvents and metal ion-free silicates, the said compositions comprising

5

(A) at least one thioamino acid having at least one primary amino group and at least one mercapto group,

(B) at least one quaternary ammonium hydroxide,

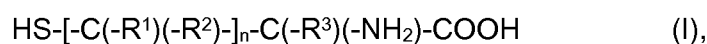
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(C) at least one chelating and/or corrosion inhibiting agent selected from the group consisting of aliphatic and cycloaliphatic amines having at least two primary amino groups, and aliphatic and cycloaliphatic amines having at least one hydroxy group,

15

(D) at least one nonionic surfactant selected from the group of acetylenic alcohols, alkyloxylated acetylenic alcohols and alkyloxylated sorbitan monocarboxylic acid mono esters.

- 20 2. The aqueous alkaline cleaning compositions according to claim 1, wherein the amino acid (A) has the general formula I:



25 wherein the index and the variables have the following meaning:

n integer of 1 to 3;

R¹ and R² selected independently from each other from the group consisting of

30

- hydrogen atoms;
- straight and branched; saturated and unsaturated, substituted and unsubstituted aliphatic residues having 1 to 10 carbon atoms;
- substituted and unsubstituted, saturated and unsaturated cycloalkyl residues having 3 to 8 carbon atoms;

35

- substituted and unsubstituted, saturated and unsaturated alkylcycloalkyl residues wherein the alkyl group is having from 1 to 4 carbon atoms and the cycloalkyl group is having from 3 to 8 carbon atoms;
- 5 - substituted and unsubstituted aryl having from 6 to 16 carbon atoms;
- substituted and unsubstituted alkylaryl residues wherein the alkyl group is having from 1 to 4 carbon atoms and the arylgroup is having from 6 to 16 carbon atoms;
- 10 - substituted and unsubstituted cycloalkylaryl residues wherein the cycloalkyl group is having from 3 to 8 carbon atoms and the arylgroup is having from 6 to 16 carbon atoms;
- substituted and unsubstituted heteroaryl residues having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms;
- 15 - substituted and unsubstituted alkylheteroaryl residues wherein the alkyl group is having from 1 to 4 carbon atoms and the heteroaryl group is having having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms;
- 20 - substituted and unsubstituted cycloalkylheteroaryl residues wherein the cycloalkyl group is having from 3 to 8 carbon atoms and the heteroaryl group is having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms
- 25 - substituted and unsubstituted arylheteroaryl residues wherein the aryl group is having from 6 to 16 carbon atoms and the heteroaryl group is having at least one hetero atom selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms or, alternatively,
- 30
- R¹ and R² together forming a saturated or unsaturated, substituted or unsubstituted ring having 3 to 6 carbon atoms, wherein no carbon atom or 1 or 2 carbon atoms is or are replaced by one hetero atom
- 35

selected from the group consisting of oxygen, sulfur, nitrogen and phosphorus atoms;

5 R^3 single residue R^1 or R^2 or covalent bond or bivalent group linking the carbon atom carrying the amino group and the carboxyl group to one of the residues R^1 or R^2 or to the ring formed by the residues R^1 and R^2 .

10 3. The aqueous alkaline cleaning composition according to claim 2, wherein the thioamino acid (A) is a racemic or an enantiomeric mixture or one of the respective enantiomers or diastereomers.

15 4. The aqueous alkaline cleaning composition according to claim 3, wherein at least one of the residues R^1 , R^2 and R^3 is a hydrogen atom.

5. The aqueous alkaline cleaning composition according to claim 4, wherein all the the residues R^1 , R^2 and R^3 of the thioamino acid (A) are hydrogen atoms.

20 6. The aqueous alkaline cleaning composition according to claim 5, wherein the thioamino acid (A) is L-cysteine.

7. The aqueous alkaline cleaning composition according to anyone of the claims 1 to 6, wherein the quaternary ammonium hydroxide (B) has the general formula II:

25 $N(-R^1)_4^+ OH^-$ (II),

30 wherein the residue R^1 is having the above defined meaning except hydrogen atom, whilst all the residues R^1 are the same or at least two residues R^1 are different from each other and all the residues R^1 are single residues or at least two residues R^1 form a saturated or unsaturated, substituted or unsubstituted ring having 3 to 6 carbon atoms, wherein no carbon atom or 1 or 2 carbon atoms are replaced by one hetero atom selected from the group of oxygen, sulfur, nitrogen and phosphorus atoms.

35 8. The aqueous alkaline cleaning composition according to claim 7, wherein the residue R^1 of the general formula (II) is methyl.

9. The aqueous alkaline cleaning composition according to anyone of the claims 1 to 8, wherein the aliphatic amine (C) having at least two primary amino groups is selected from the group consisting of ethylenediamine, propylenediamine, n-butylendiamine, diethylenetriamine, dipropylenetriamine, di-n-butylenetriamine, triethylenetetraamine, tripropylenetetraamine, and tri-n-butylenetetraamine; the cycloaliphatic amine (C) is selected from the group consisting of 1,2-, 1,3- and 1,4-diamino cyclohexane; the aliphatic amine (C) having at least one hydroxy group is selected from the group consisting of ethanolamine, diethanolamine and triethanolamine; and the cycloaliphatic amine (C) having at least one hydroxy group is selected from the group consisting of 2-, 3- and 4-hydroxy cyclohexylamine.
10. The aqueous alkaline cleaning composition according to anyone of the claims 1 to 9, wherein the nonionic surfactant (D) is selected from the group consisting of acetylenic monoalcohols and diols; alkyloxylated acetylenic monoalcohols and diols; and alkyloxylated sorbitan monocarboxylic acid fatty acid mono esters.
11. Aqueous alkaline cleaning composition according to anyone of the claims 1 to 11 furthermore comprising at least one functional additive (E) which is different from the components (A), (B), (C) and (D).
12. The aqueous alkaline cleaning composition according to claim 11, wherein the functional additive (E) is selected from the group consisting of corrosion inhibitors, bases, complexing or chelating agents, film forming agents, surfactants and pH-adjusting agents.
13. A method for processing substrates useful for fabricating electrical and optical devices, said method comprising the process step of contacting the substrate surface at least once with at least one aqueous alkaline cleaning composition according to anyone of the claims 1 to 12.
14. The method according to claim 13, wherein the process step is at least one surface preparation step, pre-plaiting cleaning step, post-etch cleaning step or post-chemical polishing cleaning step.

15. The method according to claim 13 or 14, wherein the electrical devices are semiconductor integrated circuits (ICs); liquid crystal panels; organic electroluminescent panels; printed circuit boards; micro machines; DNA chips; micro plants and magnetic heads; and the optical devices are optical glasses;
5 inorganic electro-conductive films; optical integrated circuits; optical switching elements; optical waveguides; optical monocrystals; solid laser monocrystals; sapphire substrates for blue laser LEDs; semiconductor monocrystals; and glass substrates for magnetic disks.
- 10 16. The use of the aqueous alkaline cleaning composition according to anyone of the claims 1 to 12 for the processing of substrates useful for fabricating electrical and optical devices.
- 15 17. The use according to claim 16 for the surface preparation, pre-plating cleaning, post-etch cleaning and post-chemical mechanical polishing cleaning of the substrates.